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Form PTO 1449
(Modified)U.S. DEPARTMENT OF COMMERCE
PATENT AND TRADEMARK OFFICE

ATTY DOCKET NO.

247830US420 CONT

SERIAL NO.

10/762,318

~~New Cont. App.~~

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Qin-Yi TONG et al.

FILING DATE

~~Herewith~~ 01-23-2004

GROUP

~~Unassigned~~ 2823

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EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
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Joanne A. Dajao				October 13, 2005			
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